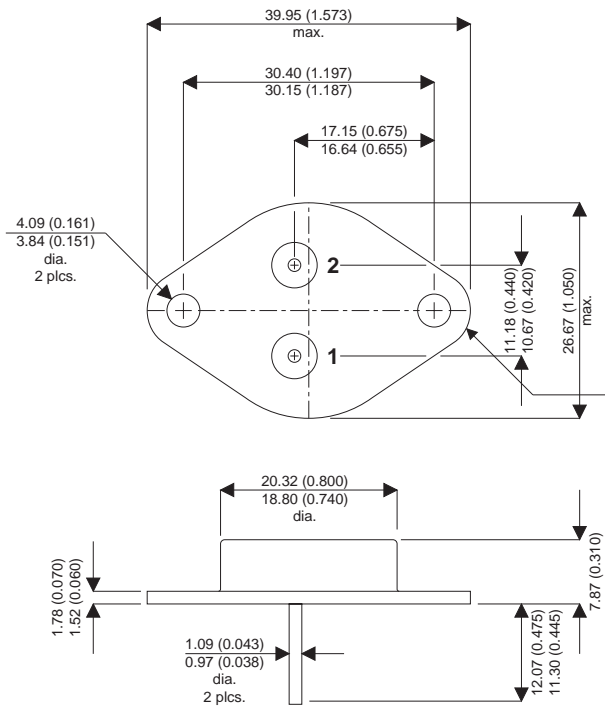


MECHANICAL DATA

Dimensions in mm (inches)



TO-3 Metal Package

Pin 1 – Gate Pin 2 – Source Case – Drain

**P-CHANNEL
POWER MOSFET**

V_{DSS} **-100V**
 $I_{D(cont)}$ **-18A**
 $R_{DS(on)}$ **0.2Ω**

FEATURES

- HERMETICALLY SEALED TO-3 METAL PACKAGE
- SIMPLE DRIVE REQUIREMENTS
- SCREENING OPTIONS AVAILABLE

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{GS}	Gate – Source Voltage	$\pm 20V$
I_D	Continuous Drain Current ($V_{GS} = 0, T_{case} = 25^{\circ}C$)	-18A
I_D	Continuous Drain Current ($V_{GS} = 0, T_{case} = 100^{\circ}C$)	-11A
I_{DM}	Pulsed Drain Current ¹	-72A
P_D	Power Dissipation @ $T_{case} = 25^{\circ}C$	125W
	Linear Derating Factor	1W/ $^{\circ}C$
E_{AS}	Single Pulse Avalanche Energy ²	500mJ
I_{AR}	Avalanche Current ²	-18A
E_{AR}	Repetitive Avalanche Energy ²	12.5mJ
dv/dt	Peak Diode Recovery ³	-5.5V/ns
T_J, T_{stg}	Operating and Storage Temperature Range	-55 to +150 $^{\circ}C$
T_L	Lead Temperature 1.6mm (0.63") from case for 10 sec.	300 $^{\circ}C$

Notes

- 1) Pulse Test: Pulse Width $\leq 300\mu s, \delta \leq 2\%$
- 2) @ $V_{DD} = -25V, L \geq 2.3mH, R_G = 25\Omega, Peak I_L = -18A, Starting T_J = 25^{\circ}C$
- 3) @ $I_{SD} \leq -18A, di/dt \leq -100A/\mu s, V_{DD} \leq BV_{DSS}, T_J \leq 150^{\circ}C, Suggested R_G = 9.1\Omega$

ELECTRICAL CHARACTERISTICS ($T_{\text{case}} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
STATIC ELECTRICAL RATINGS					
BV_{DSS} Drain – Source Breakdown Voltage	$V_{\text{GS}} = 0$ $I_{\text{D}} = -1\text{mA}$	-100			V
$\frac{\Delta BV_{\text{DSS}}}{\Delta T_{\text{J}}}$ Temperature Coefficient of Breakdown Voltage	Reference to 25°C $I_{\text{D}} = -1\text{mA}$		-0.087		$\text{V}/^{\circ}\text{C}$
$R_{\text{DS(on)}}$ Static Drain – Source On-State Resistance ¹	$V_{\text{GS}} = 10\text{V}$ $I_{\text{D}} = -11\text{A}$			0.2	Ω
	$V_{\text{GS}} = 10\text{V}$ $I_{\text{D}} = -18\text{A}$			0.23	
$V_{\text{GS(th)}}$ Gate Threshold Voltage	$V_{\text{DS}} = V_{\text{GS}}$ $I_{\text{D}} = -250\text{mA}$	-2		-4	V
g_{fs} Forward Transconductance ¹	$V_{\text{DS}} \geq -15\text{V}$ $I_{\text{DS}} = -11\text{A}$	6.2			S ($\bar{\cup}$)
I_{DSS} Zero Gate Voltage Drain Current	$V_{\text{GS}} = 0$ $V_{\text{DS}} = 0.8BV_{\text{DSS}}$ $T_{\text{J}} = 125^{\circ}\text{C}$			-25	μA
				-250	
I_{GSS} Forward Gate – Source Leakage	$V_{\text{GS}} = -20\text{V}$			-100	nA
I_{GSS} Reverse Gate – Source Leakage	$V_{\text{GS}} = 20\text{V}$			100	
DYNAMIC CHARACTERISTICS					
C_{iss} Input Capacitance	$V_{\text{GS}} = 0$		1400		pF
C_{oss} Output Capacitance	$V_{\text{DS}} = -25\text{V}$		600		
C_{riss} Reverse Transfer Capacitance	$f = 1\text{MHz}$		200		
Q_{g} Total Gate Charge	$V_{\text{GS}} = -10\text{V}$	31		60	nC
Q_{gs} Gate – Source Charge	$I_{\text{D}} = -18\text{A}$	3.7		13	
Q_{gd} Gate – Drain (“Miller”) Charge	$V_{\text{DS}} = 0.5BV_{\text{DSS}}$	7.0		35.2	
$t_{\text{d(on)}}$ Turn-On Delay Time	$V_{\text{DD}} = -50\text{V}$ $I_{\text{D}} = -18\text{A}$ $R_{\text{G}} = 9.1\Omega$			35	ns
t_{r} Rise Time				85	
$t_{\text{d(off)}}$ Turn-Off Delay Time				85	
t_{f} Fall Time				65	
SOURCE – DRAIN DIODE CHARACTERISTICS					
I_{S} Continuous Source Current				-18	A
I_{SM} Pulse Source Current ²				-72	
V_{SD} Diode Forward Voltage ¹	$I_{\text{S}} = -18\text{A}$ $T_{\text{J}} = 25^{\circ}\text{C}$ $V_{\text{GS}} = 0$			-4.2	V
t_{rr} Reverse Recovery Time ¹	$I_{\text{F}} = -18\text{A}$ $T_{\text{J}} = 25^{\circ}\text{C}$		170	280	ns
Q_{rr} Reverse Recovery Charge	$d_{\text{i}} / d_{\text{t}} \leq -100\text{A}/\mu\text{s}$ $V_{\text{DD}} \leq -50\text{V}$			3.6	μC
t_{on} Forward Turn-On Time			Negligible		
PACKAGE CHARACTERISTICS					
L_{D} Internal Drain Inductance (measured from 6mm down drain lead to centre of die)			5.0		nH
L_{S} Internal Source Inductance (from 6mm down source lead to source bond pad)			13		
THERMAL CHARACTERISTICS					
$R_{\theta\text{JC}}$ Thermal Resistance Junction – Case				1.0	$^{\circ}\text{C}/\text{W}$
$R_{\theta\text{CS}}$ Thermal Resistance Case – Sink			0.12		
$R_{\theta\text{JA}}$ Thermal Resistance Junction – Ambient				30	

Notes

- 1) Pulse Test: Pulse Width $\leq 300\text{ms}$, $\delta \leq 2\%$
- 2) Repetitive Rating – Pulse width limited by maximum junction temperature.